- ★ Super Low Gate Charge
- ★ 100% EAS Guaranteed
- ★ Green Device Available
- ★ Excellent CdV/dt effect decline
- ★ Advanced high cell density Trench technology

Product Summary

Green

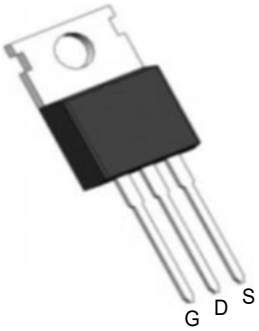
BVDSS	RDSON	ID
40V	2.7mΩ	190A

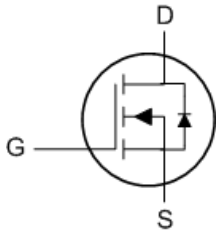
Description

The XR190N04T is the high performance complementary N-ch MOSFETs with high cell density, whichprovide excellent RDSON and gate charge for most of the synchronous buck converter applications .

The XR190N04T meet the RoHS and Green Product requirement 100% EAS guaranteed with full function reliability approved.

TO220AB Pin Configuration





Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	40	V
V_{GS}	Gate-Source Voltage	±25	V
I_D@T_C=25℃	Continuous Drain Current, V_{GS} @ 10V[1,6]	190	A
I_D@T_C=100℃	Continuous Drain Current, V_{GS} @ 10V[1,6]	123	A
I_{DM}	Pulsed Drain Current[2]	760	A
EAS	Single Pulse Avalanche Energy[3]	196	mJ
I_{AS}	Avalanche Current	28	A
P_D@T_C=25℃	Total Power Dissipation[4]	61	W
T_{STG}	Storage Temperature Range	-55 to 150	℃
T_J	Operating Junction Temperature Range	-55 to 150	℃

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-Ambient [1]	---	---	℃/W
$R_{\theta JC}$	Thermal Resistance Junction-Case[1]	---	2	℃/W

Electrical Characteristics (T_J=25 ℃, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V , I_D=250uA	40	---	---	V
$\triangle BV_{DSS}/\triangle T_J$	BV_{DSS} Temperature Coefficient	Reference to 25℃ , I_D=1mA	---	---	---	V/℃
$R_{DS(ON)}$	Static Drain-Source On-Resistance[2]	V_{GS}=10V , I_D=57A	---	2.7	3.5	mΩ
		V_{GS}=4.5V , I_D=20A	---	---	---	
$V_{GS(th)}$	Gate Threshold Voltage	V_{GS}=V_{DS} , I_D =250uA	2	2.8	4	V
$\triangle V_{GS(th)}$	$V_{GS(th)}$ Temperature Coefficient		---	---	---	mV/℃
I_{DSS}	Drain-Source Leakage Current	V_{DS}=40V , V_{GS}=0V , T_J=25℃	---	---	1	uA
		V_{DS}=40V, V_{GS}=0V , T_J=100℃	---	---	100	
I_{GSS}	Gate-Source Leakage Current	V_{GS}=±25V , V_{DS}=0V	---	---	±100	nA
gfs	Forward Transconductance	V_{DS}=5V , I_D=20A	---	---	---	S
R_g	Gate Resistance	V_{DS}=0V , V_{GS}=0V , f=1MHz	---	---	---	Ω
Q_g	Total Gate Charge	V_{DS}=20V , V_{GS}=10V , I_D=57A	---	80	---	nC
Q_{gs}	Gate-Source Charge		---	17	---	
Q_{gd}	Gate-Drain Charge		---	21	---	
$T_{d(on)}$	Turn-On Delay Time	VGS=10V, VDD=20V, RG=3Ω, RL=1Ω, ID=57A	---	21	---	ns
T_r	Rise Time		---	32	---	
$T_{d(off)}$	Turn-Off Delay Time		---	71	---	
T_f	Fall Time		---	40	---	
C_{iss}	Input Capacitance	V_{DS}=20V , V_{GS}=0V , f=1MHz	---	4900	---	pF
C_{oss}	Output Capacitance		---	528	---	
C_{rss}	Reverse Transfer Capacitance		---	317	---	

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Continuous Source Current[1,5]	V_G=V_D=0V , Force Current	---	---	190	A
V_{SD}	Diode Forward Voltage[2]	V_{GS}=0V , I_S=57A , T_J=25℃	---	---	1.2	V

Notes:1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature

2. EAS condition: T_J=25℃, V_{DD}=20V, V_G=10V, R_G=25Ω, L=0.5mH, I_{AS}=28A

3. Pulse Test: Pulse Width≤300μs, Duty Cycle≤0.5%

Typical Performance Characteristics

Figure1: Output Characteristics

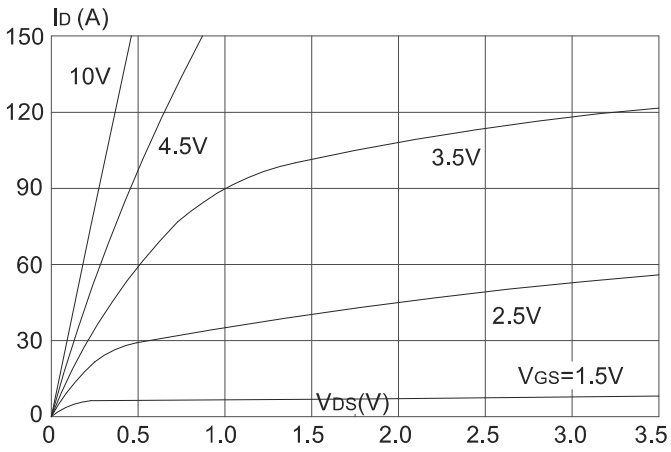


Figure 2: Typical Transfer Characteristics

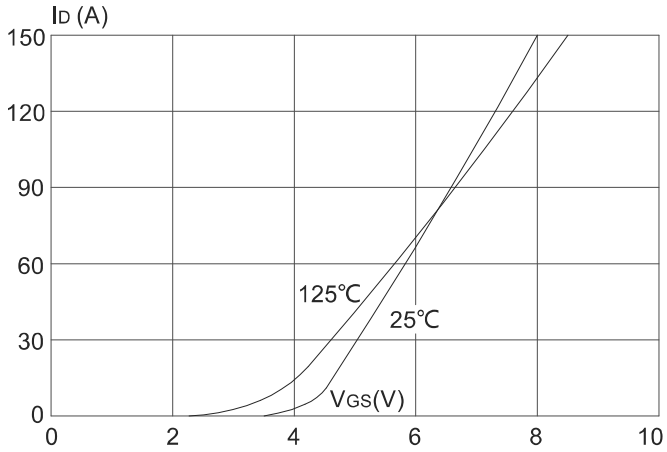


Figure 3: On-resistance vs. Drain Current

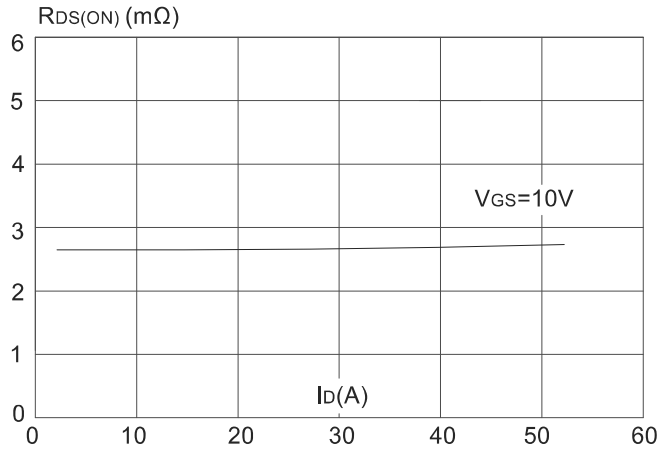


Figure 4: Body Diode Characteristics

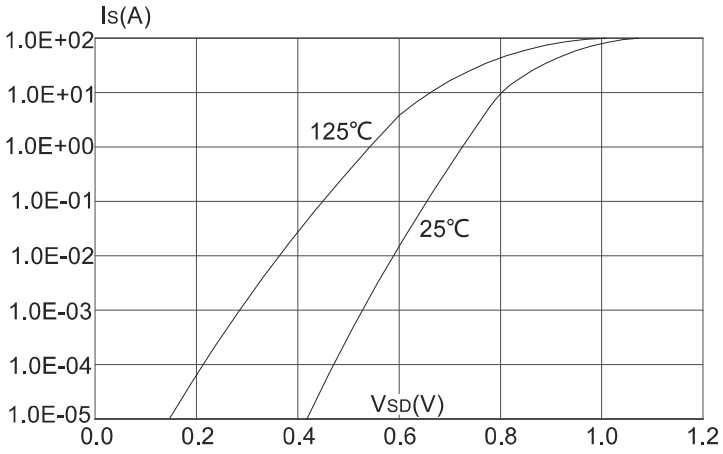


Figure 5: Gate Charge Characteristics

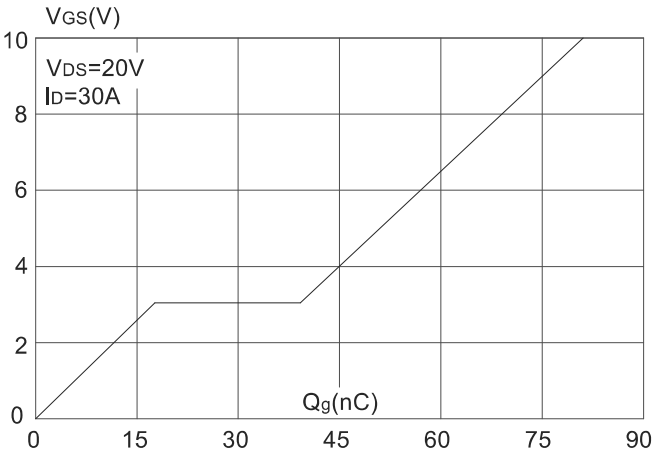


Figure 6: Capacitance Characteristics

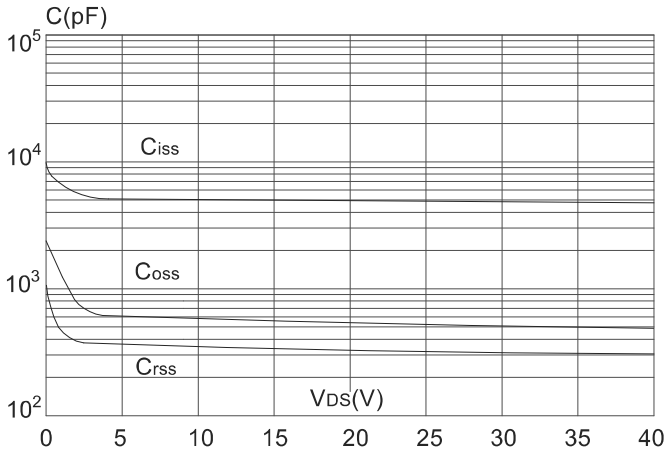


Figure 7: Normalized Breakdown Voltage vs. Junction Temperature

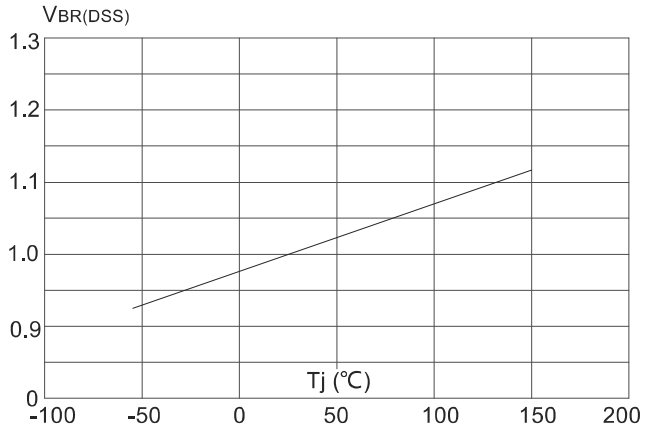


Figure 8: Normalized on Resistance vs. Junction Temperature

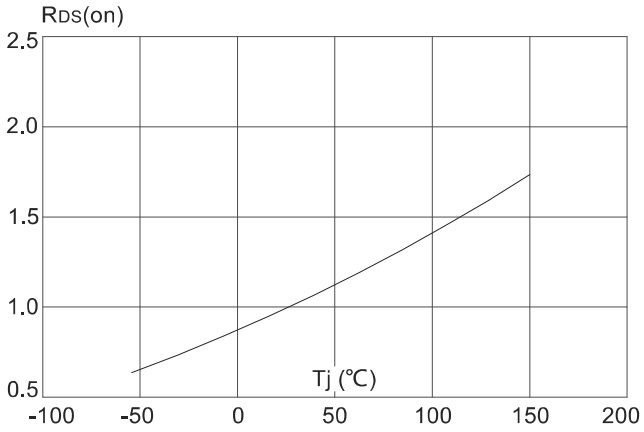


Figure 9: Maximum Safe Operating Area

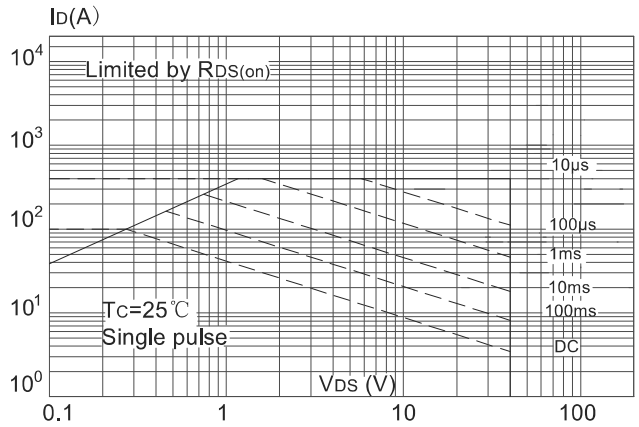


Figure 10: Maximum Continuous Drain Current vs. Case Temperature

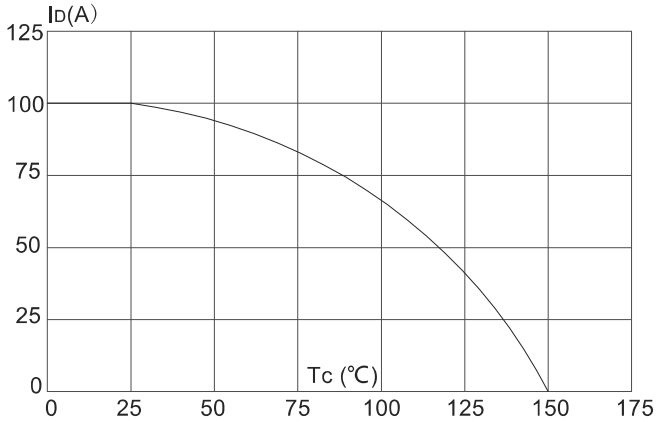
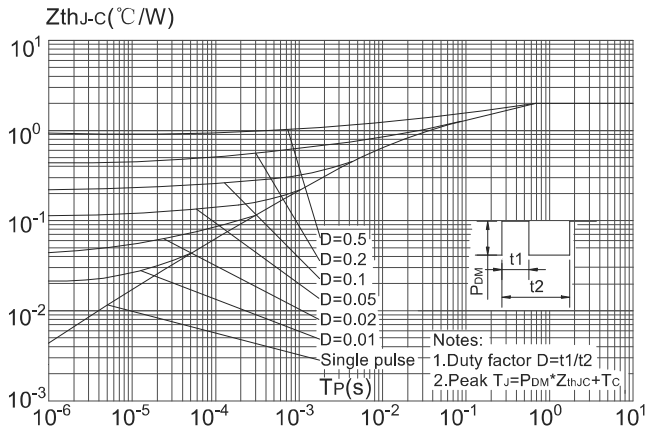
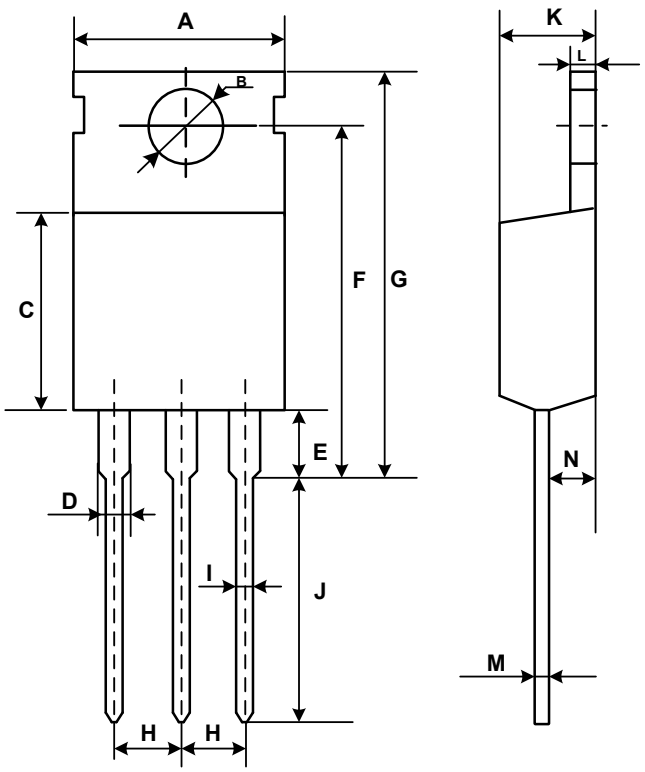


Figure.11: Maximum Effective Transient Thermal Impedance, Junction-to-Case



Mechanical Dimensions for TO-220



OMMON DIMENSIONS

SYMBOL	MM	
	MIN	MAX
A	9.70	10.30
B	3.40	3.80
C	8.80	9.40
D	1.17	1.47
E	2.60	3.50
F	15.10	16.70
G	19.55MAX	
H	2.54REF	
I	0.70	0.95
J	9.35	11.00
K	4.30	4.77
L	1.20	1.45
M	0.40	0.65
N	2.20	2.60